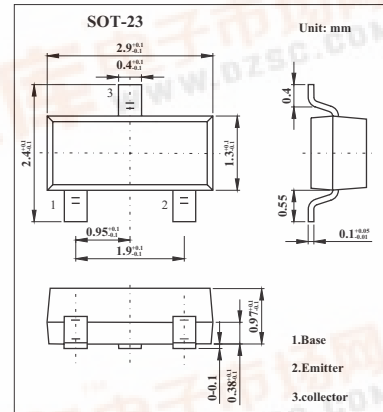


SMD Type Transistors

Silicon NPN Epitaxial
2SC2735

■ Features

-



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	30	V
Collector-emitter voltage	V _{CE0}	20	V
Emitter-base voltage	V _{EB0}	3	V
Collector current	I _c	50	mA
Collector power dissipation	P _c	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _c = 10μA, I _E = 0	30			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _c = 1mA, R _{BE} = ∞	20			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 10μA, I _c = 0	3			V
Collector cutoff current	I _{cBO}	V _{CB} = 10V, I _c = 0			0.5	μA
Collector to emitter saturation voltage	V _{CE(sat)}	I _c = 10 mA, I _B = 5 mA			1.0	V
DC current transfer ratio	h _{FE}	V _{CE} = 10 V, I _c = 5 mA	40			
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz		0.85	1.5	pF
Gain bandwidth product	CG	V _{cc} = 6 V, I _c = 2 mA, f = 900 MHz, f _{osc} = 930 MHz (0dBm), f = 30 MHz	600	1200		MHz
Oscillating output voltage	V _{osc1}	V _{cc} = 6 V, I _c = 5 mA, f = 930 MHz		210		mV
	V _{osc2}	V _{cc} = 12 V, I _c = 7 mA, f _{osc} = 930 MHz		130		mV
Conversion gain	CG	V _{cc} = 12 V, I _c = 2 mA, f = 200 MHz, f _{osc} = 230 MHz (0dBm)		21		dB
Noise figure	NF	V _{cc} = 12 V, I _c = 2 mA, f = 200 MHz, f _{osc} = 230 MHz (0dBm)		6.5		dB

■ Marking

Marking	JC
---------	----

